

IN THE CLAIMS**Amendments to the claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-8 (Canceled)

9. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

 forming an electrode pad to come in contact with a surface of a semiconductor substrate provided with a desirable element region or a wring layer provided on the surface of the semiconductor substrate;

 forming an intermediate layer on a surface of the electrode pad;

 forming a pad layer to be a bonding pad on a surface of the intermediate layer and patterning the intermediate layer and the pad layer after forming the pad layer by using a resist as a mask for patterning the pad layer and the pad layer as a mask for patterning the intermediate layer; and

 after forming the bonding pad, forming a resin insulating film to cover edges of patterns of the bonding pad and the intermediate layer, including an outer interface thereof.

10. (Original) The method of manufacturing a semiconductor device according to claim 9, wherein the step of forming a resin insulating film includes a step of applying a polyimide resin film.

11. (Previously Presented) The method of manufacturing a semiconductor device according to claim 9, wherein the step of forming an intermediate layer includes a step of forming a titanium tungsten (TiW) layer by a sputtering method.

12. (Original) The method of manufacturing a semiconductor device according to claim 11, wherein the step of forming a pad layer includes a step of forming a metal layer by sputtering.